

BCV64B

PNP general-purpose double transistor Rev. 4 — 2 August 2010

Product data sheet

Product profile

1.1 General description

PNP general-purpose double transistor in a small SOT143B Surface-Mounted Device (SMD) plastic package.

Table 1. Product overview

Type number	Package		Package		Package		PNP complement
	NXP	JEITA					
BCV64B	SOT143B	-	BCV63B				

1.2 Features and benefits

- Low current (max. 100 mA)
- Low voltage (max. 30 V and 6 V)
- AEC-Q101 qualified
- Small SMD plastic package

1.3 Applications

- General-purpose switching and amplification
- For use in Schmitt trigger applications

1.4 Quick reference data

Table 2. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per trans	istor					
I _C	collector current		-	-	-100	mA
Transisto	or TR1					
V_{CEO}	collector-emitter voltage	open base	-	-	-30	V
h _{FE}	DC current gain	$V_{CE} = -5 \text{ mV};$ $I_{C} = -2 \text{ mA}$	220	-	475	
Transisto	or TR2					
V_{CEO}	collector-emitter voltage	open base	-	-	-6	V
h _{FE}	DC current gain	$V_{CE} = -700 \text{ V};$ $I_{C} = -2 \text{ mA}$	<u>11</u> 220	-	475	

^[1] Due to matched dies, h_{FE} values for TR2 are the same as for TR1.



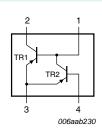
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Pinning information

Table 3. **Pinning**

Pin	Description	Simplified outline
1	collector TR2 and base TR1	
2	collector TR1	— 4 3 □ □
3	emitter TR1 and TR2	
4	base TR2	





Graphic symbol

Ordering information

Table 4. **Ordering information**

Type number	Package		
	Name	Description	Version
BCV64B	-	plastic surface-mounted package; 4 leads	SOT143B

Marking

Table 5. Marking codes

Type number	Marking code ^[1]
BCV64B	*C6

- [1] * = -: made in Hong Kong
 - * = p: made in Hong Kong
 - * = t: made in Malaysia
 - * = W: made in China

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5. Limiting values

Table 6. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
Per transi	istor				
V_{EBO}	emitter-base voltage	open collector	-	-6	V
I _C	collector current		-	-100	mA
I _{CM}	peak collector current		-	-200	mA
I_{B}	base current		-	-100	mA
Transisto	r TR1				
V_{CBO}	collector-base voltage	open emitter	-	-30	V
V_{CEO}	collector-emitter voltage	open base	-	-30	V
Transisto	r TR2				
V_{CBO}	collector-base voltage	open emitter	-	-6	V
V_{CEO}	collector-emitter voltage	open base	-	-6	V
Per devic	е				
P _{tot}	total power dissipation	$T_{amb} \le 25 ^{\circ}C$	[1] -	250	mW
Tj	junction temperature		-	150	°C
T _{amb}	ambient temperature		-65	+150	°C
T _{stg}	storage temperature		-65	+150	°C

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB).

6. Thermal characteristics

Table 7. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	<u>[1]</u> -	-	500	K/W

^[1] Device mounted on an FR4 PCB.

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7. Characteristics

Table 8. Characteristics

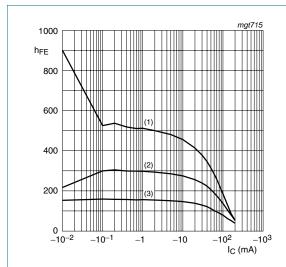
 $T_i = 25$ °C unless otherwise specified.

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per trans	sistor						
I _{CBO}	collector-base	$V_{CB} = -30 \text{ V}; I_E = 0 \text{ A}$		-	-	-15	nA
	cut-off current	$V_{CB} = -30 \text{ V}; I_E = 0 \text{ A};$ $T_j = 150 \text{ °C}$		-	-	- 5	μА
V _{CEsat}	collector-emitter saturation voltage	$I_C = -10 \text{ mA};$ $I_B = -0.5 \text{ mA}$		-	- 75	-300	mV
V_{BEsat}	base-emitter saturation voltage	$I_C = -10 \text{ mA};$ $I_B = -0.5 \text{ mA}$	[2]	-	-700	-	mV
Transisto	or TR1						
h _{FE}	DC current gain	$V_{CE} = -5 \text{ V};$ $I_{C} = -2 \text{ mA}$		220	-	475	
V _{CEsat}	collector-emitter saturation voltage	$I_C = -100 \text{ mA};$ $I_B = -5 \text{ mA}$		-	-250	-650	mV
V_{BEsat}	base-emitter saturation voltage	$I_C = -100 \text{ mA};$ $I_B = -5 \text{ mA}$	[2]	-	-850	-	mV
V_{BE}	base-emitter voltage	$I_C = -2 \text{ mA};$ $V_{CE} = -5 \text{ V}$	[3]	-600	-650	-750	mV
		$I_{C} = -10 \text{ mA};$ $V_{CE} = -5 \text{ V}$	[3]	-	-	-820	mV
f⊤	transition frequency	$V_{CE} = -5 \text{ V};$ $I_{C} = -10 \text{ mA};$ $f = 100 \text{ MHz}$		100	-	-	MHz
C _c	collector capacitance	$V_{CB} = -10 \text{ V};$ $I_E = i_e = 0 \text{ A};$ $f = 1 \text{ MHz}$		-	4	-	pF
Transisto	or TR2						
h _{FE}	DC current gain	$V_{CE} = -700 \text{ mV};$ $I_{C} = -2 \text{ mA}$	[1]	220	-	475	
V _{CEsat}	collector-emitter saturation voltage	$I_C = -100 \text{ mA};$ $I_B = -5 \text{ mA}$		-	-250	-	mV
V_{BE}	base-emitter voltage	$I_C = -2 \text{ mA};$ $V_{CE} = -700 \text{ mV}$	[3]	-	-700	-	mV

^[1] Due to matched dies, h_{FE} values for TR2 are the same as for TR1.

^[2] V_{BEsat} decreases by about 1.7 mV/K with increasing temperature.

^[3] V_{BE} decreases by about 2 mV/K with increasing temperature.



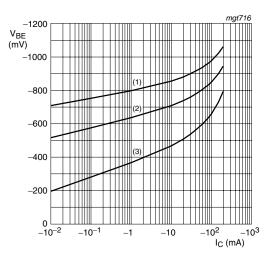
$$V_{CE} = -5 \text{ V}$$

(1)
$$T_{amb} = 150 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = -55 \, ^{\circ}C$$

Fig 1. DC current gain as a function of collector current; typical values



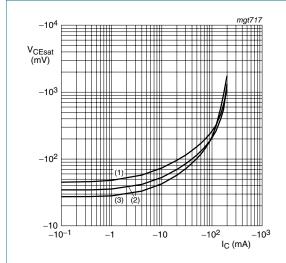
$$V_{CE} = -5 \text{ V}$$

(1)
$$T_{amb} = -55 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = 150 \, ^{\circ}C$$

Fig 2. Base-emitter voltage as a function of collector current; typical values



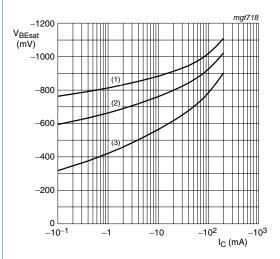
 $I_{\rm C}/I_{\rm B}=20$

(1)
$$T_{amb} = 150 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = -55 \, ^{\circ}C$$

Fig 3. Collector-emitter saturation voltage as a function of collector current; typical values



$$I_{\rm C}/I_{\rm B} = 20$$

(1)
$$T_{amb} = -55 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

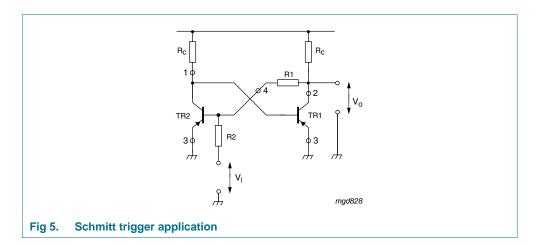
(3)
$$T_{amb} = 150 \, ^{\circ}C$$

Fig 4. Base-emitter saturation voltage as a function of collector current; typical values

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8. Application information



9. Test information

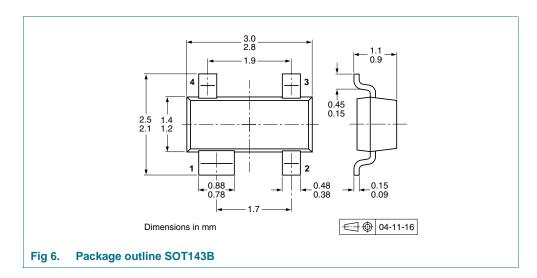
9.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

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10. Package outline



11. Packing information

Table 9. Packing methods

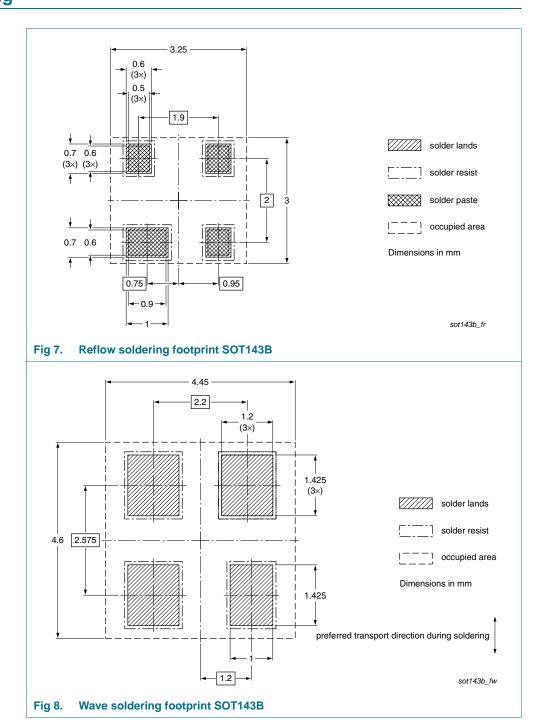
The indicated -xxx are the last three digits of the 12NC ordering code.[1]

Type number	Package	Description	Packing qu	antity
			3000	10000
BCV64B	SOT143B	4 mm pitch, 8 mm tape and reel	-215	-235

[1] For further information and the availability of packing methods, see <u>Section 15</u>.

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12. Soldering



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13. Revision history

Table 10. Revision history

Release date	Data sheet status	Change notice	Supersedes			
		Juliango notico	•			
20100802	Product data sheet	-	BCV64B_3			
		lesigned to comply w	ith the new identity			
 Legal texts h 	ave been adapted to the new	company name whe	re appropriate.			
 Section 1 "Pr 	roduct profile": amended.					
 Section 3 "Ordering information": added. 						
 <u>Section 4 "Marking"</u>: updated. 						
• Figure 1, 2, 3	and 4: added.					
Section 8 "Application information": added.						
Section 9 "Test information": added.						
 Figure 6: superseded by minimized package outline drawing. 						
 Section 11 "F 	Packing information": added.					
 Section 12 "S 	Soldering": added.					
 Section 14 "L 	<u>egal information"</u> : updated.					
19990521	Product specification	-	BCV64_CNV_2			
19970310	Product specification	-	-			
	guidelines of Legal texts h Section 1 "Pr Section 3 "O Section 4 "M Figure 1, 2, 3 Section 8 "Ar Section 9 "Te Figure 6: sup Section 11 "F Section 12 "S Section 14 "L 19990521	 The format of this data sheet has been recognidelines of NXP Semiconductors. Legal texts have been adapted to the new Section 1 "Product profile": amended. Section 3 "Ordering information": added. Section 4 "Marking": updated. Figure 1, 2, 3 and 4: added. Section 8 "Application information": added. Section 9 "Test information": added. Figure 6: superseded by minimized package. Section 11 "Packing information": added. Section 12 "Soldering": added. Section 14 "Legal information": updated. Product specification 	 The format of this data sheet has been redesigned to comply we guidelines of NXP Semiconductors. Legal texts have been adapted to the new company name whe Section 1 "Product profile": amended. Section 3 "Ordering information": added. Section 4 "Marking": updated. Figure 1, 2, 3 and 4: added. Section 9 "Test information": added. Section 11 "Packing information": added. Section 11 "Packing information": added. Section 12 "Soldering": added. Section 14 "Legal information": updated. Product specification - 			

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14. Legal information

14.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
- [3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

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